

Title (en)
SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Title (de)
HALBLEITERVORRICHTUNG UND HERSTELLUNGSVERFAHREN

Title (fr)
DISPOSITIF A SEMI-CONDUCTEURS ET PROCEDE DE FABRICATION DE CE DERNIER

Publication
EP 1122769 A4 20041013 (EN)

Application
EP 99970209 A 19991005

Priority
• JP 9905464 W 19991005
• JP 29761498 A 19981005

Abstract (en)
[origin: EP1122769A1] In a semiconductor device, a contact layer is provided between a silicon-containing insulating film SiO₂, etc. or a metal wiring layer, and a fluorine-containing carbon CF film to increase their adhesion. For this purpose, SiC film deposition gases, such as SiH₄ gas and C₂H₄ gas, are excited into plasma to stack a SiC film 200 as the contact layer on the top surface of a SiO₂ film 110. After that, switching of deposition gases is conducted for about 1 second by introducing SiH₄ gas, C₂H₄ gas, C₄F₈ gas and C₂H₄ gas. Subsequently, CF film deposition gases, such as C₄F₈ gas and C₂H₄ gas, for example, are excited into plasma to deposit a CF film 120 on the SiC film 200. In this way, both the SiC film deposition gases and the CF film deposition gases exist simultaneously during the deposition gas switching step, whereby Si-C bonds are produced near the boundary between the SiC film 200 and the CF film 120 across these films, and they enhance adhesion between these films and hence increase adhesion of the SiO₂ film 110 and the CF film 120. <IMAGE>

IPC 1-7
H01L 21/314; **H01L 21/768**

IPC 8 full level
H01L 21/768 (2006.01); **H01L 21/31** (2006.01); **H01L 21/312** (2006.01); **H01L 21/314** (2006.01); **H01L 23/522** (2006.01); **H01L 23/532** (2006.01); **H01L 21/04** (2006.01); **H01L 21/316** (2006.01)

CPC (source: EP KR US)
H01L 21/0212 (2013.01 - EP KR US); **H01L 21/02164** (2013.01 - EP KR US); **H01L 21/02167** (2013.01 - EP KR US);
H01L 21/0217 (2013.01 - EP KR US); **H01L 21/022** (2013.01 - EP KR US); **H01L 21/02211** (2013.01 - EP KR US);
H01L 21/02274 (2013.01 - KR US); **H01L 21/02304** (2013.01 - EP KR US); **H01L 21/3127** (2013.01 - US); **H01L 23/53295** (2013.01 - EP US);
H01L 21/02274 (2013.01 - EP); **H01L 21/0445** (2013.01 - EP US); **H01L 21/3146** (2013.01 - US); **H01L 21/31612** (2013.01 - US);
H01L 2924/0002 (2013.01 - EP US)

C-Set (source: EP US)
H01L 2924/0002 + **H01L 2924/00**

Citation (search report)
• [XA] EP 0701283 A2 19960313 - NEC CORP [JP]
• [XA] WO 9821748 A1 19980522 - TOKYO ELECTRON LTD [JP], et al & US 6218299 B1 20010417 - AKAHORI TAKASHI [JP], et al
• [XA] JP H10223625 A 19980821 - NEC CORP & US 6091081 A 20000718 - MATSUBARA YOSHIHISA [JP], et al
• See also references of WO 0021124A1

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Designated contracting state (EPC)
BE DE FR GB IT NL

DOCDB simple family (publication)
EP 1122769 A1 20010808; **EP 1122769 A4 20041013**; JP 2000114252 A 20000421; JP 4361625 B2 20091111; KR 100414297 B1 20040107; KR 20010075566 A 20010809; TW 429428 B 20010411; US 6429518 B1 20020806; WO 0021124 A1 20000413

DOCDB simple family (application)
EP 99970209 A 19991005; JP 29761498 A 19981005; JP 9905464 W 19991005; KR 20017004239 A 20010403; TW 88117137 A 19991005; US 65934200 A 20000912